

### GTR Module

### Silicon N Channel IGBT

### High Power Switching Applications

### Motor Control Applications

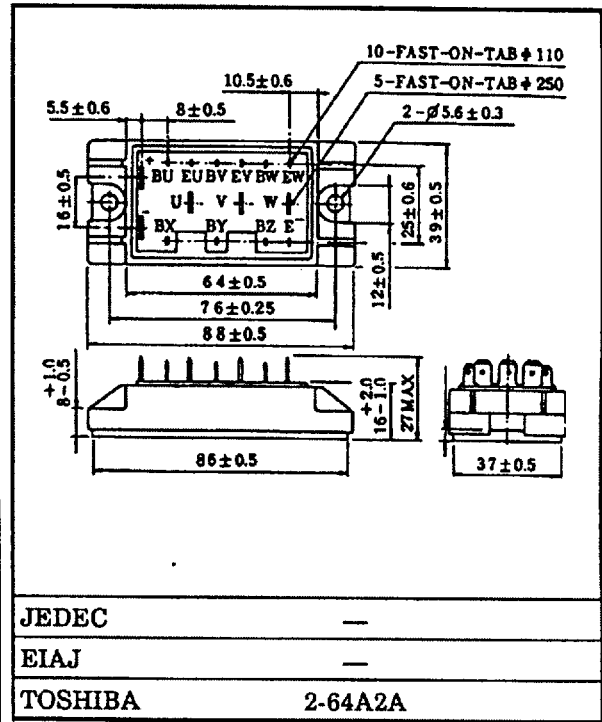
#### Features

- 6 IGBTs are built into 1 package
- High speed:  $t_f = 0.35\mu\text{s}$  (Max.) ( $I_C = 15\text{A}$ )  
 $t_{rr} = 0.15\mu\text{s}$  (Max.) ( $I_C = 15\text{A}$ )
- Low saturation voltage:  $V_{CE(sat)} = 3.5\text{V}$  (Max.) ( $I_F = 15\text{A}$ )
- Enhancement mode
- The electrodes are isolated from case

#### Maximum Ratings ( $T_c = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	$V_{CES}$	600	V
Gate-Emitter Voltage	$V_{GES}$	$\pm 20$	V
Collector Current	DC	$I_C$	15
	1ms	$I_{CP}$	30
Forward Current	DC	$I_F$	15
	1ms	$I_{FM}$	30
Collector Power Dissipation	$P_C$	80	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-40 ~ 125	$^\circ\text{C}$
Isolation Voltage	$V_{isol}$	2500 (AC 1 Minute)	V
Screw Torque	—	3	N ¥ m

Unit in mm



Weight : 152g

